

Kun Cao

List of Publications by Year in descending order

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papers

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1684188
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10
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26
citing authors

#	ARTICLE	IF	CITATIONS
1	Improvement of crystalline quality of CdZnTe epilayers on GaAs(001) substrates with a two-step growth by Close Spaced Sublimation. Vacuum, 2019, 164, 319-324.	3.5	23
2	The growth of CdZnTe epitaxial thick film by close spaced sublimation for radiation detector. Vacuum, 2019, 168, 108852.	3.5	12
3	Nucleation and islands growth of CdZnTe(0 $\bar{1}$ 1) epitaxial films on GaAs(0 $\bar{1}$ 1) substrates by close spaced sublimation. Journal of Crystal Growth, 2018, 498, 197-201.	1.5	9
4	Origin and evolution of threading dislocation in CdZnTe(0 $\bar{1}$ 1)/GaAs(0 $\bar{1}$ 1) epilayer grown by close spaced sublimation. Applied Surface Science, 2020, 504, 144431.	6.1	6
5	Preparation of Cd _{0.8} Zn _{0.2} Te/Cd _{0.5} Zn _{0.5} Te/n+-GaAs thick film radiation detectors by close spaced sublimation. Vacuum, 2021, 192, 110426.	3.5	6
6	Analysis of Dislocations in CdZnTe Epitaxial Film with Kelvin Probe and Conductive Atomic Force Microscopy. Journal of Electronic Materials, 2020, 49, 3907-3912.	2.2	5
7	The effect of chemical polishing treatment on the microstructure, photoelectric properties of CdZnTe polycrystalline films. Materials Science in Semiconductor Processing, 2021, 124, 105608.	4.0	5
8	Effects of annealing on the properties of CdZnTe epitaxial thick films deposited on p-GaAs using close-spaced sublimation. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2021, 1015, 165752.	1.6	4
9	An alternative GaSb substrate allowing close-spaced sublimation of Cd _{0.9} Zn _{0.1} Te epitaxial thick film for radiation detectors. Materials Science in Semiconductor Processing, 2022, 147, 106688.	4.0	4
10	Cracking mechanism of CdZnTe polycrystalline film deposited on TFT circuit board at high temperature by close-spaced sublimation method. Materials Science in Semiconductor Processing, 2021, 131, 105821.	4.0	1